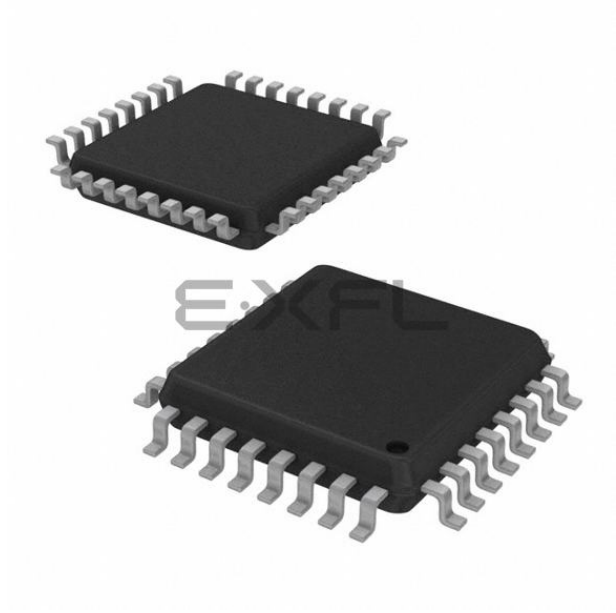

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	26
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l011k4t6d

List of figures

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM® Cortex®-M4, including ARM® Cortex®-M3 and ARM® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 Ultra-low-power series are the best solution for applications such as gas/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power Run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

3 Functional overview

3.1 Low-power modes

The ultra-low-power STM32L011x3/4 supports dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

- **Low-power run mode**

  This mode is achieved with the multispeed internal (MSI) RC oscillator set to the low-speed clock (max 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Low-power run mode, the clock frequency and the number of enabled peripherals are both limited.

- **Low-power sleep mode**

  This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

  When wakeup is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

- **Stop mode with RTC**

  The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSE and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

  Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

  The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event

3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

The BOOT0 pin is shared with PB9 GPIO pin. This pin is an input-only pin. If nBOOT_SEL option bit is reset, sampling this pin on NRST rising edge gives the internal BOOT0 state. This pin then works as PB9 pin. The input voltage characteristics of this pin are specific for BOOT0 pin type (see *Table 50: I/O static characteristics*).

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event

3.12 Ultra-low-power comparators and reference voltage

The STM32L011x3/4 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
  - External I/O pins
  - Internal reference voltage (V_{REFINT})
  - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

3.13 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21 and LPTIM1 timer input captures. It also controls the routing of internal analog signals to the ADC, COMP1 and COMP2 and the internal reference voltage V_{REFINT}.

3.14 Timers and watchdogs

The ultra-low-power STM32L011x3/4 devices include two general-purpose timers, one low-power timer (LPTIM1), two watchdog timers and the SysTick timer.

Table 7 compares the features of the general-purpose and basic timers.

Table 7. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No

3.14.1 General-purpose timers (TIM2, TIM21)

There are three synchronizable general-purpose timers embedded in the STM32L011x3/4 devices (see *Table 7* for differences).

TIM2

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 general-purpose timer via the Timer Link feature for synchronization or event chaining. Its counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM21

TIM21 is based on a 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It has two independent channels for input capture/output compare, PWM or one-pulse mode output. It can work together and be synchronized with TIM2 full-featured general-purpose timer.

It can also be used as simple timebase and be clocked by the LSE clock source (32.768 kHz) to provide independent timebase from the main CPU clock.

3.14.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
  - Internal clock source: LSE, LSI, HSI or APB clock
  - External clock source over LPTIM1 input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

3.14.3 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches ‘0’.

Table 9. STM32L011x3/4 I²C implementation

I2C features[1]	I2C1
7-bit addressing mode	X
10-bit addressing mode	X
Standard mode (up to 100 kbit/s)	X
Fast mode (up to 400 kbit/s)	X
Fast Mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s)	X[2]
Independent clock	X
SMBus	X
Wakeup from STOP	X

1. X = supported.
2. See *Table 13: Pin definitions on page 37* for the list of I/Os that feature Fast Mode Plus capability

3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

The USART interface (USART2) is able to communicate at speeds of up to 4 Mbit/s.

It provides hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode and single-wire half-duplex communication mode. USART2 also supports Smartcard communication (ISO 7816, T=0 protocol) and IrDA SIR ENDEC.

USART2 interface can be served by the DMA controller.

Table 10 for the supported modes and features of USART interface.

Table 10. USART implementation

USART modes/features[1]	USART2
Hardware flow control for modem	X
Continuous communication using DMA	X
Multiprocessor communication	X
Synchronous mode	-
Smartcard mode	X
Single-wire half-duplex communication	X
IrDA SIR ENDEC block	X
LIN mode	-
Dual clock domain and wakeup from Stop mode	-
Receiver timeout interrupt	-
Modbus communication	-
Auto baud rate detection (4 modes)	-
Driver Enable	X

1. X = supported.

Table 13. Pin definitions (continued)

Pin number							Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
TSSOP14	UFQFPN20	TSSOP20	UFQFPN28	LQFP32	UFQFPN32[1]	WLCSP25					Alternate functions	Additional functions
-	-	-	26	28	28	-	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM21_CH1	COMP2_INP
-	18	-	27	29	29	A3	PB6	I/O	FTf	-	USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM2_CH3, LPUART1_TX	COMP2_INP
-	19	-	28	30	30	A4	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2, TIM2_CH4, LPUART1_RX	COMP2_INP, VREF_PVD_IN
1	20	1	1	31	31	A5	PB9-BOOT0	I	B	-	-	BOOT0 (Boot memory selection)
-	-	-	-	-	32	-	PB8	I/O	FTf	-	USART2_TX, EVENTOUT, I2C1_SCL, SPI1_NSS	-
-	-	-	-	32	-	-	VSS	S	-	(5)	-	-
-	-	-	-	1	1	-	VDD	S	-	(6)	-	-

1. V_{SS} pins are connected to the exposed pad (see *Figure 36: UFQFPN32, 5 x 5 mm, 32-pin package outline*).
2. Device reset input/internal reset output (active low).
3. Analog power supply.
4. On TSSOP14 package, V_{DDA} is internally connected to V_{DD}.
5. Digital and analog ground.
6. Digital power supply.

Table 19. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	V
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results, not tested in production.
2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Table 22. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0]=11	1 MHz	140	180	µA
				2 MHz	245	290	
				4 MHz	460	540	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10,	4 MHz	0.56	0.65	mA
				8 MHz	1.1	1.3	
				16 MHz	2.1	2.4	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	1.3	1.6	
				16 MHz	2.6	3	
				32 MHz	5.3	6.5	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	34.5	54	µA
				524 kHz	86	120	
				4.2 MHz	505	560	
		HSI clock	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10,	16 MHz	2.2	2.6	mA
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	5.4	5.9	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 23. Current consumption in Run mode vs code type, code with data processing running from Flash

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(1)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	460	µA
				CoreMark		440	
				Fibonacci		330	
				while(1)		305	
				while(1), prefetch OFF		320	
			Range 1, VOS[1:0]=01, V_{CORE}=1.8 V	Dhrystone	32 MHz	5.4	mA
				CoreMark		4.9	
				Fibonacci		5	
				while(1)		4.35	
				while(1), prefetch OFF		3.7	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 26. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	36.5	70	µA
				2 MHz	58	95	
				4 MHz	100	150	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	125	170	
				8 MHz	230	300	
				16 MHz	450	540	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	275	350	
				16 MHz	555	650	
				32 MHz	1350	1600	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	15.5	32	
				524 kHz	26.5	55	
				4.2 MHz	115	160	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	585	670	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	49	88	
				2 MHz	69	120	
				4 MHz	115	190	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	135	200	
				8 MHz	240	340	
				16 MHz	460	650	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	290	400	
				16 MHz	565	750	
				32 MHz	1350	1900	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	26.5	46	
				524 kHz	38.5	70	
				4.2 MHz	125	190	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	600	760	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1850	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 27. Current consumption in Low-power Run mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (LP Run)	Supply current in Low-power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	5.7	8.1	µA
				T_A = 85 °C	6.5	9	
				T_A = 105 °C	8	13	
				T_A = 125 °C	11.5	22	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	8.7	11	
				T_A = 85 °C	9.5	12	
				T_A = 105 °C	11	15	
				T_A = 125 °C	15	24	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	17	19	
				T_A = 55 °C	17	19.5	
				T_A = 85 °C	17.5	20	
				T_A = 105 °C	19	22	
				T_A = 125 °C	22.5	31	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	18	22	
				T_A = 85 °C	20	24	
				T_A = 105 °C	22	27	
				T_A = 125 °C	26.5	37	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	22	25	
				T_A = 85 °C	24	27	
				T_A = 105 °C	26	30	
				T_A = 125 °C	30.5	39	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	32	34	
				T_A = 55 °C	32.5	35	
				T_A = 85 °C	34	37	
				T_A = 105 °C	36	39	
				T_A = 125 °C	40	47	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.

Table 33. Peripheral current consumption in Stop and Standby mode

Symbol	Peripheral	Typical consumption, T_A = 25 °C		Unit
		V_{DD}=1.8 V	V_{DD}=3.0 V	
$I_{DD(PVD / BOR)}$	-	0.6	1	µA
I_{REFINT}	-	1.25	1.3	
-	LSE Low drive	0.11	0.16	
-	LPTIM1, Input 100 Hz	0.01	0.02	
-	LPTIM1, Input 1 MHz	8	9	
-	LPUART1	0.025	0.027	
-	RTC	0.1	0.19	

6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 18*.

Table 34. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	f_{HCLK} = 32 MHz	7	8	CPU cycles
$t_{WUSLEEP\_LP}$	Wakeup from Low-power sleep mode, f_{HCLK} = 262 kHz	f_{HCLK} = 262 kHz Flash enabled	7	8	
		f_{HCLK} = 262 kHz Flash switched OFF	9	10	

Table 34. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz	5.1	8	µs
		$f_{HCLK} = f_{HSI}$ = 16 MHz	5.1	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.1	11	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 1	5	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 2	5	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 3	5	8	
		$f_{HCLK} = f_{MSI}$ = 2.1 MHz	7.4	13	
		$f_{HCLK} = f_{MSI}$ = 1.05 MHz	14	23	
		$f_{HCLK} = f_{MSI}$ = 524 kHz	28	38	
		$f_{HCLK} = f_{MSI}$ = 262 kHz	51	65	
		$f_{HCLK} = f_{MSI}$ = 131 kHz	99	120	
		$f_{HCLK} = f_{MSI}$ = 65 kHz	196	260	
		$f_{HCLK} = f_{HSI}$ = 16 MHz	5.1	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.2	11	
	Wakeup from Stop mode, regulator in low-power mode, HSI kept running in Stop mode	$f_{HCLK} = f_{HSI}$ = 16 MHz	3.25	-	
	Wakeup from Stop mode, regulator in low-power mode, code running from RAM	$f_{HCLK} = f_{HSI}$ = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	7.9	10	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz	4.8	8	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI}$ = 2.1 MHz	65	130	
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI}$ = 2.1 MHz	2.2	3	ms

Low-speed internal (LSI) RC oscillator

Table 39. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(1)	LSI frequency	26	38	56	kHz
D_{LSI}(2)	LSI oscillator frequency drift 0°C ≤ T_A ≤ 85°C	-10	-	4	%
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design, not tested in production.

Multi-speed internal (MSI) RC oscillator

Table 40. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at V_{DD}= 3.3 V and T_A = 25 °C	MSI range 0	65.5	-	kHz
		MSI range 1	131	-	
		MSI range 2	262	-	
		MSI range 3	524	-	
		MSI range 4	1.05	-	MHz
		MSI range 5	2.1	-	
		MSI range 6	4.2	-	
ACC_{MSI}	Frequency error after factory calibration	-	±0.5	-	%
$D_{TEMP(MSI)}$(1)	MSI oscillator frequency drift 0 °C ≤ T_A ≤ 85 °C	-	±3	-	%
$D_{VOLT(MSI)}$(1)	MSI oscillator frequency drift 1.65 V ≤ V_{DD} ≤ 3.6 V, T_A = 25 °C	-	-	2.5	%/V
$I_{DD(MSI)}$(2)	MSI oscillator power consumption	MSI range 0	0.75	-	µA
		MSI range 1	1	-	
		MSI range 2	1.5	-	
		MSI range 3	2.5	-	
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	

Flash memory and data EEPROM

Table 43. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
V_{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t_{prog}	Programming time for word or half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during the whole programming / erase operation	T_A = 25 °C, V_{DD} = 3.6 V	-	500	700	µA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design, not tested in production.

Table 44. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{CYC}(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	kcycles
	Cycling (erase / write) EEPROM data memory		100	
	Cycling (erase / write) Program memory	T_A = -40°C to 125 °C	0.2	
	Cycling (erase / write) EEPROM data memory		2	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	T_{RET} = +85 °C	30	years
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 85 °C		30	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	T_{RET} = +105 °C	10	
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 105 °C			
	Data retention (program memory) after 200 cycles at T_A = 125 °C	T_{RET} = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T_A = 125 °C			

1. Guaranteed by characterization results, not tested in production.
2. Characterization is done according to JEDEC JESD22-A117.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 46. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range (32 MHz voltage Range 1)	Unit
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP32 package compliant with IEC 61967-2	0.1 to 30 MHz	-22	dBµV
			30 to 130 MHz	-7	
			130 MHz to 1GHz	-12	
			SAE EMI Level	1	-

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 47. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	

1. Guaranteed by characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 48. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +125 °C conforming to JESD78A	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence oscillator frequency deviation).

The test results are given in the *Table 49*.

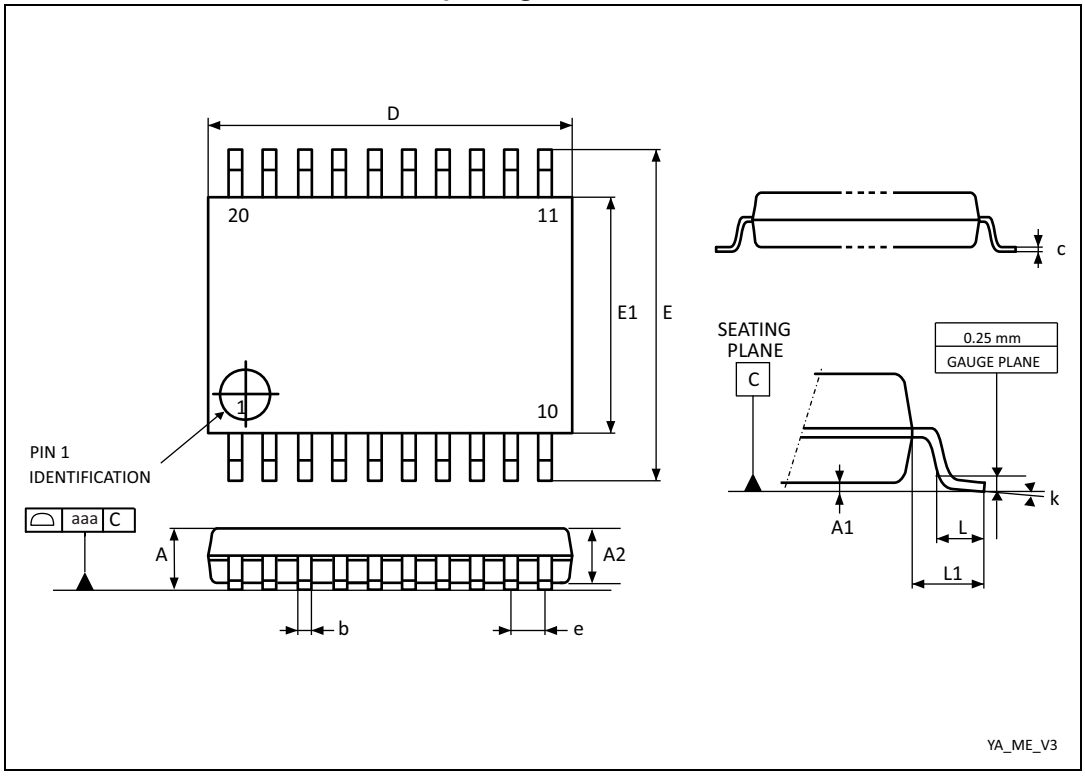
Table 49. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	-0	NA	mA
	Injected current on all FT pins	-5 (1)	NA	
	Injected current on any other pin	-5 (1)	+5	

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

7.6 TSSOP20 package information

Figure 48.TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package outline



1. Drawing is not to scale.

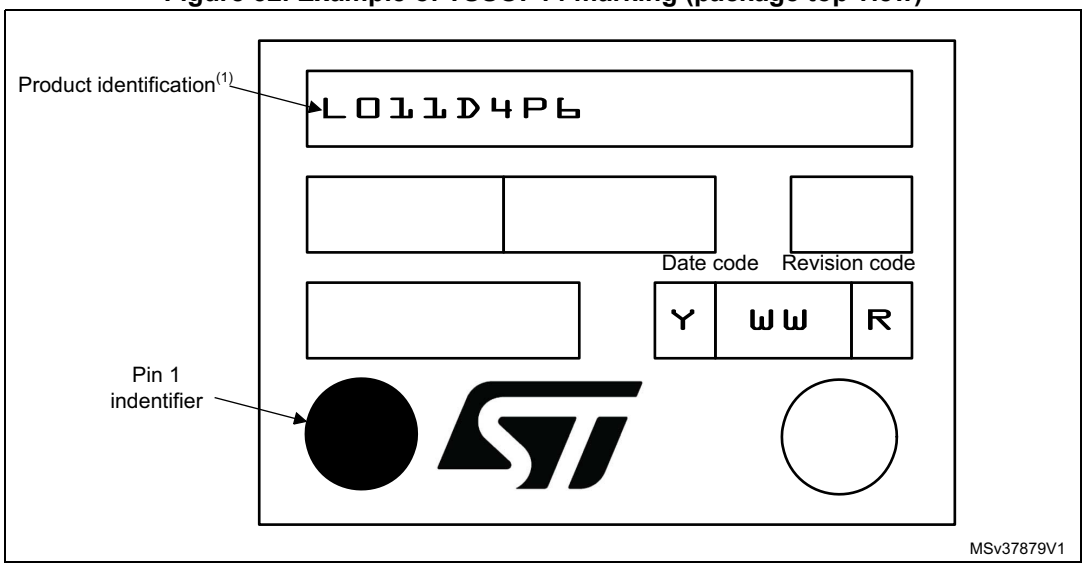
Table 74. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package mechanical data

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
D	6.400	6.500	6.600	0.2520	0.2559	0.2598
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1	4.300	4.400	4.500	0.1693	0.1732	0.1772
e	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-

TSSOP14 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 52. Example of TSSOP14 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.8 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max × Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.